



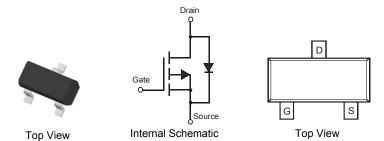
#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
  - $60m\Omega$  @  $V_{GS} = -4.5V$
  - $90m\Omega$  @  $V_{GS} = -2.5V$
  - $113m\Omega$  @  $V_{GS} = -1.8V$
- Low Input Capacitance
- Fast Switching Speed Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



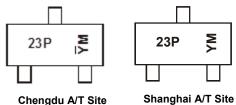
### Ordering Information (Note 4&5)

Part Number	rt Number Qualification Case		Packaging	
DMP2305U-7	Standard	SOT23	3000/Tape & Reel	
DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**



Shanghai A/T Site

23P = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

October 2013

Y or  $\overline{Y}$  = Year (ex: A =  $2\overline{0}13$ )

M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 6) Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	-4.2 -3.4	А
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	-10	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

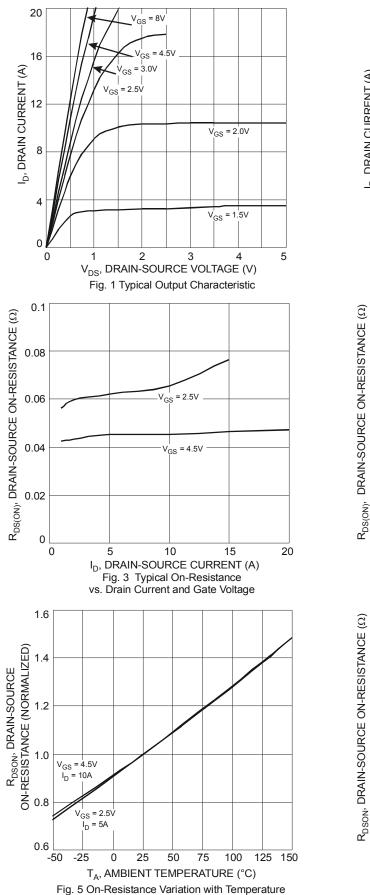
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

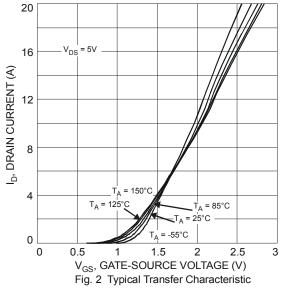
Characteristic	Symbol	Min	Tyn	Max	Unit	Test Condition	
	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition	
OFF CHARACTERISTICS (Note 8)			ı	ı		1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			45	60		$V_{GS} = -4.5V$ , $I_{D} = -4.2A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	60	90	mΩ	$V_{GS} = -2.5V$ , $I_{D} = -3.4A$	
	,		87	113		$V_{GS} = -1.8V$ , $I_{D} = -2.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	727	_	pF	14 0014 14 014	
Output Capacitance	Coss	_	69	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	64	_	pF	-1 = 1.0WH2	
Gate Resistance	R <sub>G</sub>		23		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Qq		7.6	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	1.4	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -4V$ , $I_{D} = -3.5A$	
Gate-Drain Charge	$Q_{gd}$	_	1.2	_	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	_	14.0		ns		
Turn-On Rise Time	t <sub>r</sub>	_	13.0	_	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	53.8		ns	$R_L = 4\Omega$ , $R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>f</sub>	_	23.2	_	ns		

Notes:

- 6. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width  $t \le 10s$ .
- Repetitive rating, pulse width limited by junction temperature.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.







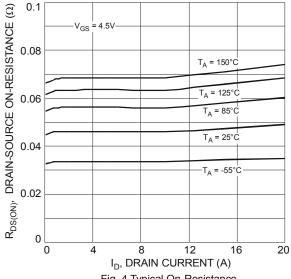


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

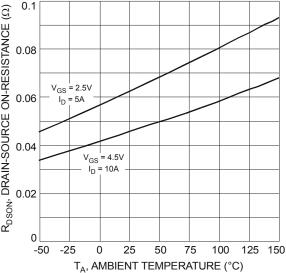


Fig. 6 On-Resistance Variation with Temperature



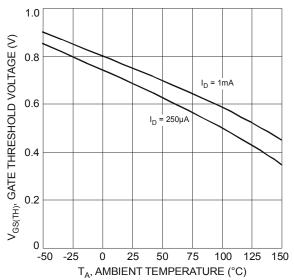
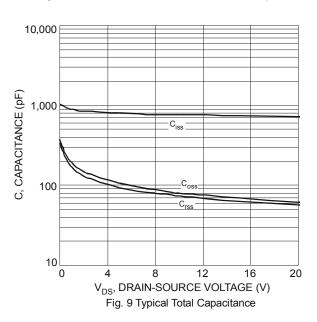
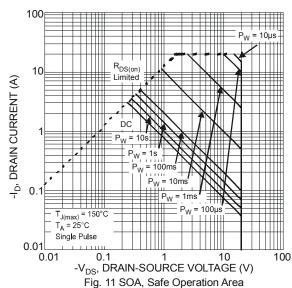
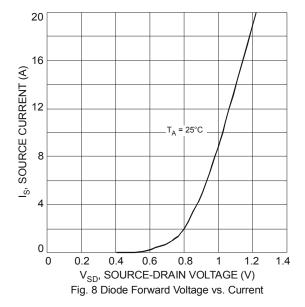


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







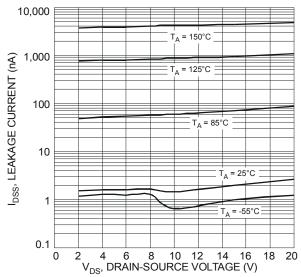
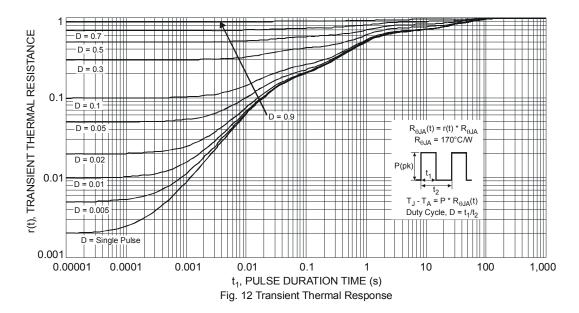


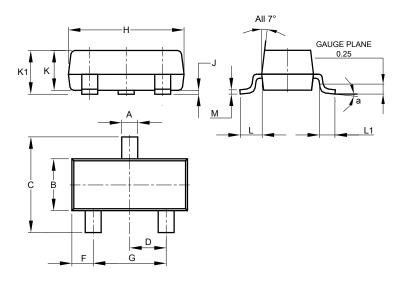
Fig. 10 Typical Leakage Current vs. Drain-Source Voltage





# **Package Outline Dimensions**

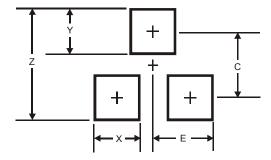
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Min Max Ty						
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
α	8°							
All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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